

Notice of References Cited		Application/Control No.	Applicant(s)/Patent Under Reexamination	
		10/771,023	LUNG, HSIANG LAN	
Examiner		Art Unit	Eric Wendler	

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NON-PATENT DOCUMENTS

*	Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)		
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.